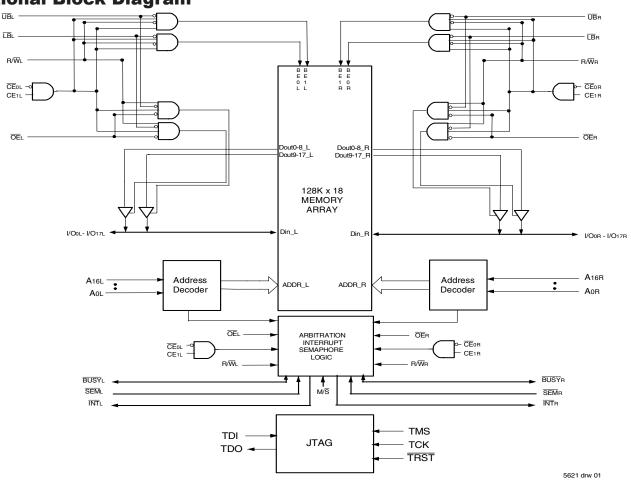
HIGH-SPEED 3.3V 128K x 18 ASYNCHRONOUS DUAL-PORT STATIC RAM

Features

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed access
 - Commercial: 10/12/15ns (max.)
 - Industrial: 12/15ns (max.)
- Dual chip enables allow for depth expansion without external logic
- IDT70V639 easily expands data bus width to 36 bits or more using the Master/Slave select when cascading more than one device
- M/S = VIH for BUSY output flag on Master, M/S = VIL for BUSY input on Slave
- Busy and Interrupt Flags
- On-chip port arbitration logic
- Full on-chip hardware support of semaphore signaling between ports

Functional Block Diagram

- Fully asynchronous operation from either port
- Separate byte controls for multiplexed bus and bus matching compatibility
- Supports JTAG features compliant to IEEE 1149.1
 Due to limited pin count, JTAG is not supported on the
 - 128-pin TQFP package.
- LVTTL-compatible, single 3.3V (±150mV) power supply for core
- LVTTL-compatible, selectable 3.3V (±150mV)/2.5V (±100mV) power supply for I/Os and control signals on each port
- Available in a 128-pin Thin Quad Flatpack, 208-ball fine pitch Ball Grid Array, and 256-ball Ball Grid Array
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information



NOTES:

- 1. BUSY is an input as a Slave (M/S=VL) and an output when it is a Master (M/S=VH).
- 2. BUSY and INT are non-tri-state totem-pole outputs (push-pull).

JUNE 2015

IDT70V639S

High-Speed 3.3V 128K x 18 Asynchronous Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

5621 tbl 02b

Description

The IDT70V639 is a high-speed 128K x 18 Asynchronous Dual-Port Static RAM. The IDT70V639 is designed to be used as a stand-alone 2304K-bit Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 36-bit-or-more word system. Using the IDT MASTER/ SLAVE Dual-Port RAM approach in 36-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

This device provides two independent ports with separate control,

address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature controlled by the chip enables (either CE0 or CE1) permit the on-chip circuitry of each port to enter a very low standby power mode.

The 70V639 can support an operating voltage of either 3.3V or 2.5V on one or both ports, controlled by the OPT pins. The power supply for the core of the device (VDD) remains at 3.3V.

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	
А	I/O9L	NC	Vss	TDO	NC	A16L	A12L	Asl	NC	VDD	SEM∟	ĪNT∟	A4L	Aol	OPT∟	NC	Vss	А
в	NC	Vss	NC	TDI	NC	A13L	A9L	NC	CEOL	Vss	BUSY∟	A5L	A1L	Vss	VDDQR	I/O8L	NC	в
С	VDDQL	I/O9R	VDDQR	Vdd	NC	A14L	A10L	ŪB∟	CE1L	Vss	R/₩L	A6L	A2L	VDD	I/O8R	NC	Vss	С
D	NC	Vss	I/O10L	NC	A15L	A11L	A7∟	ĒΒι	VDD	ŌĒL	NC	A _{3L}	VDD	NC	VDDQL	I/O7L	I/O7R	D
Е	I/O11L	NC	VDDQR	I/O10R										I/O6L	NC	Vss	NC	Е
F	VDDQL	I/O11R	NC	Vss										Vss	I/O _{6R}	NC	Vddqr	F
G	NC	Vss	I/O12L	NC										NC	VDDQL	I/O _{5L}	NC	G
н	VDD	NC	VDDQR	I/O12R					V639 F208					Vdd	NC	Vss	I/O5R	н
J	VDDQL	VDD	Vss	Vss				208-	Ball	BGA				Vss	VDD	Vss	Vddqr	J
к	I/O14R	Vss	I/O13R	Vss					o Vie					I/O3r	Vddql	I/O _{4R}	Vss	к
L	NC	I/O14L	Vddqr	I/O13L										NC	I/O3L	Vss	I/O4L	L
М	VDDQL	NC	I/O15R	Vss										Vss	NC	I/O2R	Vddqr	м
Ν	NC	Vss	NC	I/O15L		-		-	-		-			I/O1R	Vddql	NC	I/O2L	Ν
Р	I/O16R	I/O16L	VDDQR	NC	TRST	A16R	A 12R	Asr	NC	VDD	SEMR	ĪNTR	A4R	NC	I/O1L	Vss	NC	Ρ
R	Vss	NC	I/O178	тск	NC	A13R	A9R	NC	CEOR	Vss	BUSYR	A5R	A1R	Vss	Vddql	I/Oor	VDDQR	R
т	NC	I/O17L	VDDQL	тмз	NC	A14R	A10R	ŪBR	CE1R	Vss	R/\overline{W}_R	A6R	A2R	Vss	NC	Vss	NC	т
U	Vss	NC	VDD	NC	A 15R	A118	A7R	ĒBr	VDD	ŌĒr	M/S	Азя	Aor	VDD	OPTR	NC	I/Ool	U

Pin Configurations^(1,2,3,4)

NOTES:

3. All Vss pins must be connected to ground.

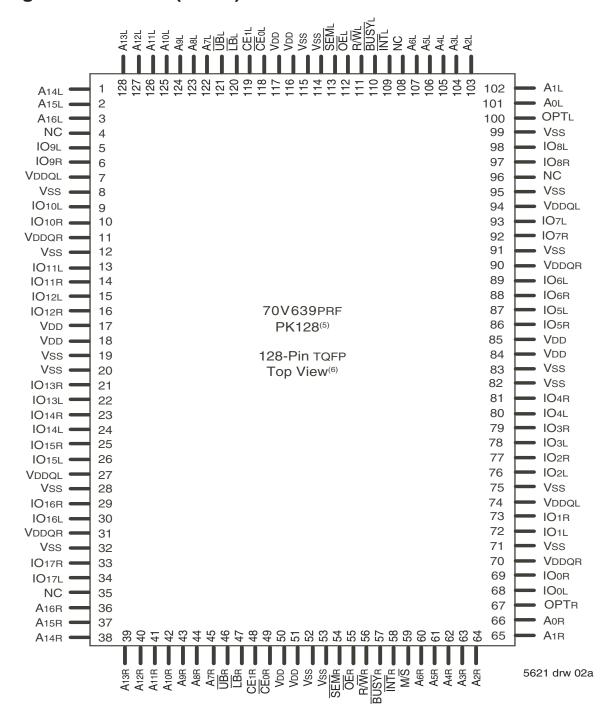
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

^{1.} All VDD pins must be connected to 3.3V power supply.

^{2.} All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V) and 2.5V if OPT pin for that port is set to VIL (0V).

^{4.} Package body is approximately 15mm x 15mm x 1.4mm with 0.8mm ball pitch.

Pin Configurations^(1,2,3,4,7) (con't.)



- 1. All VDD pins must be connected to 3.3V power supply.
- All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V) and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground.
- 4. Package body is approximately 14mm x 20mm x 1.4mm.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.
- 7. Due to the restricted number of pins, JTAG is not supported in the PK128 package.

IDT70V639S

High-Speed 3.3V 128K x 18 Asynchronous Dual-Port Static RAM

Pin Configuration^(1,2,3,4) (con't.)

70V639BC BC256⁽⁵⁾

256-Pin BGA Top View⁽⁶⁾

A1	^{A2}	A3	A4	A5	A6	A7	A8	^{A9}	A10	a11	A12	A13	A14	A15	A16
NC	TDI	NC	NC	A 14L	A11L	A8L	NC	CE1L	OEL	INTl	A 5L	A2L	A0L	NC	NC
B1 NC	^{B2} NC	^{B3} TDO	^{B4} NC	B5 A15L	B6 A12L	B7 A9L	B8 UBl		B10 R/WL	B11 NC	B12 A 4L	B13 A1L	^{B14} NC	B15 NC	^{B16} NC
C1	C2	C3	C4	C5	C6	C7	C8	C9	^{C10}	C11	C12	С13	^{C14}	C15	C16
NC	I/O9∟	Vss	A16L	A13L	A10L	A7L	NC	LBL	SEM∟	BUSY∟	A 6L	А з∟	OPT∟	NC	I/O8∟
D1	d2	D3	d4	d5	d6	d7	d8	d9	d10	d11	d12	D13	D14	D15	D16
NC	I/O9r	NC	Vdd	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vdd	NC	NC	I/O8R
e1	e2	E3	e4	e5	e6	e7	^{E8}	^{E9}	E10	E11	E12	e13	E14	e15	e16
I/O10r	I/O10L	NC	Vddql	Vdd	Vdd	Vss	Vss	Vss	Vss	VDD	VDD	Vddqr	NC	I/O7l	I/O7r
F1	F2	F3	f4	F5	F6	F7	^{F8}	F9	F10	F11	F12	f13	F14	F15	F16
I/O11L	NC	I/O11R	Vddql	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddqr	I/O6R	NC	I/O6L
G1	G2	G3	g4	G5	G6	G7	G8	^{G9}	G10	G11	G12	g13	G14	G15	G16
NC	NC	I/O12L	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	VSS	Vddql	I/ O 5L	NC	NC
H1	h2	нз	h4	H5	H6	H7	H8	H9	H10	H11	H12	h13	H14	H15	h16
NC	I/O12R	NC	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	NC	NC	I/O5r
J1	J2	јз	j4	J5	J6	J7	_{J8}	^{J9}	J10	J11	J12	j13	j14	J15	J16
I/O13∟	I/O14R	I/O13R	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O4r	I/Oзr	I/O4L
кı	к2	кз	k4	к5	к ₆	к7	ка	кэ	K10	K11	K12	k13	K14	к15	к16
NC	NC	I/O14L	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	NC	NC	І/Оз∟
l1	L2	l3	l4	l5	L6	L7	L8	L9	L10	L11	L12	l13	l14	L15	l/O2r
I/O15l	NC	I/O15R	Vddqr	Vdd	VSS	Vss	Vss	Vss	Vss	Vss	Vdd	Vddql	I/O2l	NC	
м1	m2	^{мз}	^{M4}	M5	M6	M7	^{M8}	^{M9}	M10	M11	M12	M13	м14	м15	M16
I/O16R	I/O16L	NC	Vddqr	Vdd	Vdd	Vss	Vss	Vss	Vss	VDD	Vdd	Vddql	I/O1r	I/O1L	NC
N1	^{N2}	N3	^{N4}	^{N5}	n6	n7	n8	n9	n10	N11	n12	N13	N14	N15	N16
NC	I/O17R	NC	Vdd	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vdd	NC	I/Oor	NC
P1	Р2	P3	P4	P5	P6	P7	P8	P9	^{P10}	P11	P12	Р13	P14	P15	P16
NC	I/O17L	TMS	A16R	A13R	A10R	A 7R	NC	LBR	SEMR	BUSYR	A 6R	А 3R	NC	NC	I/Oo∟
R1	^{R2}	^{R3}	^{R4}	R5	R6	R7	r8	R9	^{R10}	^{R11}	R12	R13	^{R14}	^{R15}	^{R16} NC
NC	NC	TRST	NC	A15R	A12R	A9R	UBr	CEOR	R/Wr	M/S	A 4R	A 1R	OPTr	NC	
T1	T2	^{тз}	T4	T5	т6	T7	T8	^{T9}	T10	^{t11}	T12	T13	T14	^{T15}	^{т16}
NC	TCK	NC	NC	A14R	А11R	A 8R	NC	CE1R	OEr	INTr	A 5R	A 2R	A 0R	NC	NC

NOTES:

1. All VDD pins must be connected to 3.3V power supply.

2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).

3. All Vss pins must be connected to ground supply.

4. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.

5. This package code is used to reference the package diagram.

6. This text does not indicate orientation of the actual part-marking.

5621 drw 02c

Pin Names

Left Port	Names	
Ē€0L, CE1L	\overline{CE}_{0R} , CE1R	Chip Enables
R/₩L	R/Wr	Read/Write Enable
ŌĒL	ŌĒr	Output Enable
Aol - A16l	A0R - A16R	Address
1/Ool - 1/O17l	I/O0r - I/O17r	Data Input/Output
SEML	SEMR	Semaphore Enable
ĪNTL	ĪNTR	Interrupt Flag
BUSYL	BUSYR	Busy Flag
ŪBL	ŪBR	Upper Byte Select
L BL	LBR	Lower Byte Select
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽¹⁾
OPT∟	OPTR	Option for selecting VDDQX ^(1,2)
I	M/S	Master or Slave Select
,	VDD	Power (3.3V) ⁽¹⁾
,	Vss	Ground (0V)
	TDI	Test Data Input
1	ГDO	Test Data Output
	ICK	Test Logic Clock (10MHz)
1	MS	Test Mode Select
Ŧ	RST	Reset (Initialize TAP Controller)

5621 tbl 01

- 1. VDD, OPTx, and VDDQx must be set to appropriate operating levels prior to applying inputs on I/Ox.
- 2. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to VIH (3.3V), then that port's I/Os and controls will operate at 3.3V levels and VDDQx must be supplied at 3.3V. If OPTx is set to VIL (0V), then that port's I/Os and controls will operate at 2.5V levels and VDDQx must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.

IDT70V639S High-Speed 3.3V 128K x 18 Asynchronous Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Truth Table I—Read/Write and Enable Control⁽¹⁾

ŌĒ	SEM	Ē	CE1	ŪB	ΓB	R/W	Byte 1 I/O9-17	Byte 0 I/O0-8	MODE
Х	Н	Н	Х	Х	Х	Х	High-Z	High-Z	Deselected–Power Down
Х	Н	Х	L	Х	Х	Х	High-Z	High-Z	Deselected–Power Down
Х	Н	L	Н	Н	Н	Х	High-Z	High-Z	Both Bytes Deselected
Х	Н	L	Н	Н	L	L	High-Z	DIN	Write to Byte 0 Only
Х	Н	L	Н	Ц	Н	L	Din	High-Z	Write to Byte 1 Only
Х	Н	L	Н	Ц	L	L	Din	DIN	Write to Both Bytes
L	Н	L	Н	Н	L	Н	High-Z	Dout	Read Byte 0 Only
L	Н	L	Н	L	Н	Н	Dout	High-Z	Read Byte 1 Only
L	Н	L	Н	L	L	Н	Dout	Dout	Read Both Bytes
Н	Н	L	Н	L	L	Х	High-Z	High-Z	Outputs Disabled

NOTE:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

5621 tbl 02

Truth Table II – Semaphore Read/Write Control⁽¹⁾

		Inpu	uts ⁽¹⁾			Out	puts	
CE ⁽²⁾	R/W	ŌĒ	ŪB	ĹΒ	SEM	I/O 1-17	I/Oo	Mode
Н	Н	L	L	L	L	DATAOUT	DATAOUT	Read Data in Semaphore Flag ⁽³⁾
Н	Ŷ	Х	Х	L	L	Х	DATAIN	Write I/Oo into Semaphore Flag
L	Х	Х	Х	Х	L			Not Allowed
								5621 tbl 03

NOTES:

1. There are eight semaphore flags written to I/Oo and read from all the I/Os (I/Oo-I/O17). These eight semaphore flags are addressed by Ao-A2.

2. \overline{CE} = L occurs when \overline{CE}_0 = VIL and CE1 = VIH.

3. Each byte is controlled by the respective \overline{UB} or \overline{LB} . To read data \overline{UB} and/or \overline{LB} = VIL.

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 150mV
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 150mV

NOTE:

1. This is the parameter TA. This is the "instant on" case temperature.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
TBIAS ⁽³⁾	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	٥C
Tjn	Junction Temperature	+150	٥c
Ιουτ	DC Output Current	50	mA
			5621 tbl 05

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. VTERM must not exceed VDD + 150mV for more than 25% of the cycle time or 4ns maximum, and is limited to \leq 20mA for the period of VTERM \geq VDD + 150mV.

3. Ambient Temperature Under Bias. No AC Conditions. Chip Deselected.

Capacitance⁽¹⁾

(TA = +25°C, F = 1.0MHz) TQFP ONLY

Symbol	Parameter	Conditions	Max.	Unit
Cin	Input Capacitance	VIN = 0V	8	pF
Cout ⁽²⁾	Output Capacitance	Vout = 0V	10.5	pF
				5621 tbl 08

NOTES:

1. These parameters are determined by device characterization, but are not production tested.

2. COUT also references CI/O.

Industrial and Commercial Temperature Ranges

5621 tbl 06

Recommended DC Operating Conditions with VDDQ at 2.5V

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vdd	Core Supply Voltage	3.15	3.3	3.45	٧
VDDQ	I/O Supply Voltage ⁽³⁾	2.4	2.5	2.6	۷
Vss	Ground	0	0	0	۷
Vih	Input High Voltage ⁽³⁾ (Address & Control Inputs)	1.7		Vddq + 100mV ⁽²⁾	V
V⊪	Input High Voltage - I/O ⁽³⁾	1.7	—	$V_{DDQ} + 100 mV^{(2)}$	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾		0.7	V

NOTES:

5621 tbl 04

1. VIL \geq -1.5V for pulse width less than 10 ns.

2. VTERM must not exceed VDDQ + 100mV.

 To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIL (0V), and VDDax for that port must be supplied as indicated above.

Recommended DC Operating Conditions with VDDQ at 3.3V

Symbol	Parameter	Min.	Тур.	Max.	Unit			
Vdd	Core Supply Voltage	3.15	3.3	3.45	V			
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	V			
Vss	Ground	0	0	0	V			
V⊪	Input High Voltage (Address & Control Inputs) ⁽³⁾	2.0		Vddq + 150mV ⁽²⁾	V			
V⊪	Input High Voltage - I/O ⁽³⁾	2.0	_	V_{DDQ} + 150mV ⁽²⁾	V			
VIL	Input Low Voltage	-0.3(1)	_	0.8	V			
NOTEO	5621 tbl 07							

NOTES:

1. VIL \geq -1.5V for pulse width less than 10 ns.

 To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIH (3.3V), and VDDax for that port must be supplied as indicated above.

^{2.} VTERM must not exceed VDDQ + 150mV.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 3.3V ± 150mV)

			70V	639S	
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
lu	Input Leakage Current ⁽¹⁾	VDDQ = Max., VIN = 0V to VDDQ		10	μA
llo	Output Leakage Current	\overline{CE}_0 = ViH or CE1 = ViL, Vout = 0V to VDDQ		10	μA
Vol (3.3V)	Output Low Voltage ⁽²⁾	IOL = +4mA, VDDQ = Min.		0.4	V
Voн (3.3V)	Output High Voltage ⁽²⁾	IOH = -4mA, VDDQ = Min.	2.4	—	V
Vol (2.5V)	Output Low Voltage ⁽²⁾	IoL = +2mA, VDDQ = Min.		0.4	V
Voн (2.5V)	Output High Voltage ⁽²⁾	IOH = -2mA, VDDQ = Min.	2.0	_	V

NOTES:

1. At VDD \leq - 2.0V input leakages are undefined.

2. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.5 for details.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽³⁾ (VDD = 3.3V ± 150mV)

					·			/			
						39S10 Only	Co	39S12 m'l Ind	70V639S15 Com'l & Ind		
Symbol	Parameter	Test Condition	Versio	Version		Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit
IDD	Dynamic Operating	CEL and CER= VIL,	COM'L	S	340	500	315	465	300	440	mA
	Current (Both Ports Active)	Outputs Disabled, f = fMAX ⁽¹⁾	IND	S			365	515	350	490	
ISB1	Standby Current	$\overline{CEL} = \overline{CER} = VIH$	COM'L	S	115	165	90	125	75	100	mA
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	S			115	150	100	125	
ISB2	Standby Current (One Port - TTL	\overline{CE} "A" = VIL and \overline{CE} "B" = VIH ⁽⁵⁾	COM'L	S	225	340	200	325	175	315	mA
	Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S			225	365	200	350	
ISB3	Full Standby Current (Both Ports - CMOS	Both Ports CEL and CER ≥ VDDQ - 0.2V,	COM'L	S	3	15	3	15	3	15	mA
	Level Inputs)	$ \begin{array}{l} \text{VIN} \geq \text{VDDQ} - 0.2 \text{V or VIN} \leq 0.2 \text{V}, \\ \text{f} = 0^{(2)} \end{array} $	IND	S			6	15	6	15	
ISB4	Full Standby Current (One Port - CMOS Level Inputs)	CE [*] / _A " ≤ 0.2V and CE [*] / _B " ≥ VDDQ - 0.2V ⁽⁵⁾ VIN > VDDQ - 0.2V or VIN < 0.2V,	COM'L	S	220	335	195	320	170	310	mA
		Active Port, Outputs Disabled, $f = fMAX^{(1)}$	IND	S			220	360	195	345	

5621 tbl 10

5621 tbl 09

NOTES:

1. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/tRc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

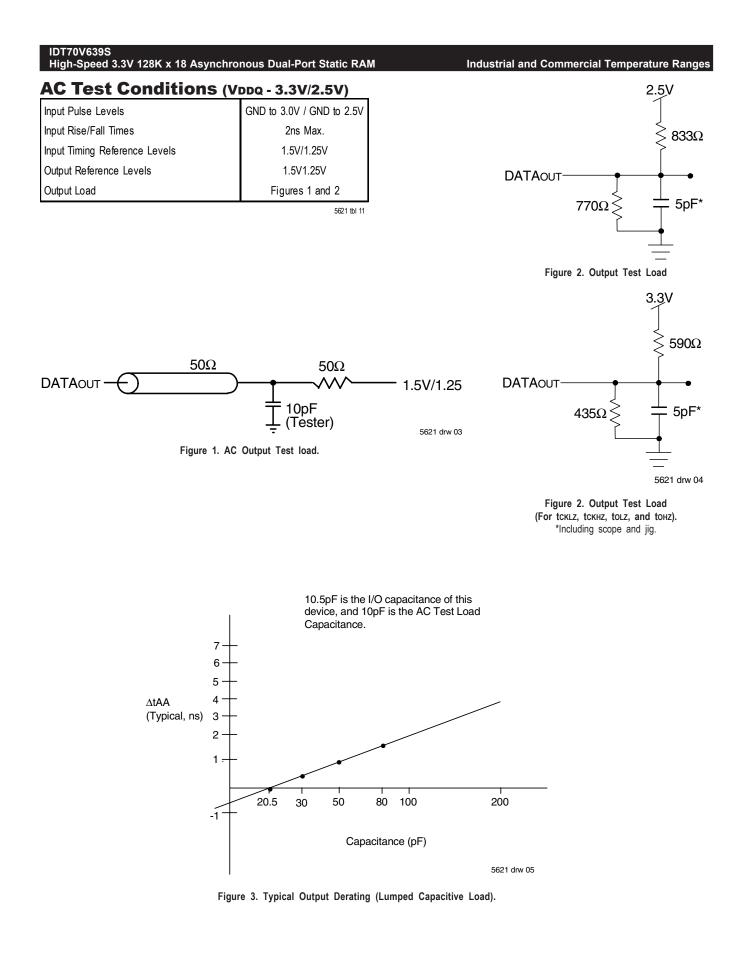
4. VDD = 3.3V, TA = 25°C for Typ, and are not production tested. IDD DC(f=0) = 120mA (Typ).

- 5. $\overline{CE}x = VIL$ means $\overline{CE}0x = VIL$ and CE1x = VIH
 - $\overline{CE}x = VIH$ means $\overline{CE}0x = VIH$ or CE1x = VIL

 $\overline{\text{CE}}x \leq 0.2 \text{V}$ means $\overline{\text{CE}}\textsc{oset} x \leq 0.2 \text{V}$ and $\text{CE}\textsc{iset} x \geq \text{V}\textsc{dog}$ - 0.2V

 $\overline{CE}x \ge V_{DDQ} - 0.2V$ means $\overline{CE}_{0X} \ge V_{DDQ} - 0.2V$ or CE1x - 0.2V

"X" represents "L" for left port or "R" for right port.



AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁵⁾

			70V639S10 Com'l Only		70V639S12 Com'l & Ind		70V639S15 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	
READ CYCLE									
tRC	Read Cycle Time	10		12		15		ns	
tAA	Address Access Time		10		12		15	ns	
tACE	Chip Enable Access Time ⁽³⁾		10		12		15	ns	
t ABE	Byte Enable Access Time ⁽³⁾		5		6	-	7	ns	
tAOE	Output Enable Access Time		5		6		7	ns	
tон	Output Hold from Address Change	3		3		3		ns	
tLZ	Output Low-Z Time ^(1,2)	0		0		0		ns	
tHZ	Output High-Z Time ^(1,2)	0	4	0	6	0	8	ns	
t₽U	Chip Enable to Power Up Time ⁽²⁾	0	_	0		0		ns	
t PD	Chip Disable to Power Down Time ⁽²⁾		10		10		15	ns	
tSOP	Semaphore Flag Update Pulse (OE or SEM)		4		6		8	ns	
tsaa	Semaphore Address Access Time	3	10	3	12	3	20	ns	

5621 tbl 12

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽⁵⁾

			70V639S10 Com'l Only		70V639S12 Com'l & Ind		70V639S15 Com'l & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE	E							
twc	Write Cycle Time	10		12		15		ns
tew	Chip Enable to End-of-Write ⁽³⁾	8		10		12		ns
taw	Address Valid to End-of-Write	8		10		12		ns
tAS	Address Set-up Time ⁽³⁾	0		0		0		ns
twp	Write Pulse Width	8		10		12		ns
twR	Write Recovery Time	0		0		0		ns
tow	Data Valid to End-of-Write	6		8		10		ns
tDH	Data Hold Time ⁽⁴⁾	0		0		0		ns
twz	Write Enable to Output in High-Z ^(1,2)	—	4		4		4	ns
tow	Output Active from End-of-Write ^(1,2,4)	0		0		0		ns
tswrd	SEM Flag Write to Read Time	5		5		5		ns
tsps	SEM Flag Contention Window	5		5		5		ns
	·	-	-	-	-	-		5621 tbl 13

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

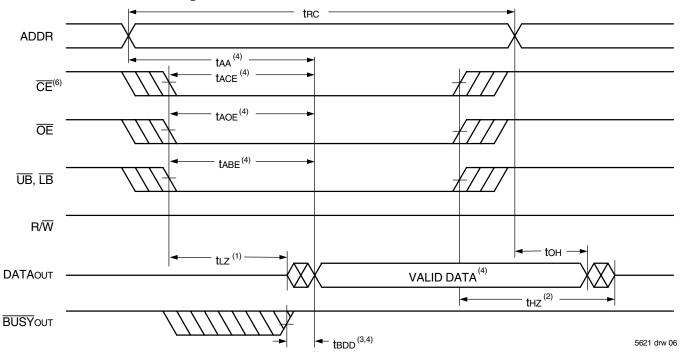
2. This parameter is guaranteed by device characterization, but is not production tested.

3. To access RAM, \overline{CE} = VIL and \overline{SEM} = VIH. To access semaphore, \overline{CE} = VIH and \overline{SEM} = VIL. Either condition must be valid for the entire tew time.

4. The specification for tDH must be met by the device supplying write data to the RAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.

5. These values are valid regardless of the power supply level selected for I/O and control signals (3.3V/2.5V). See page 5 for details.

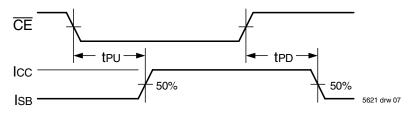
Waveform of Read Cycles⁽⁵⁾



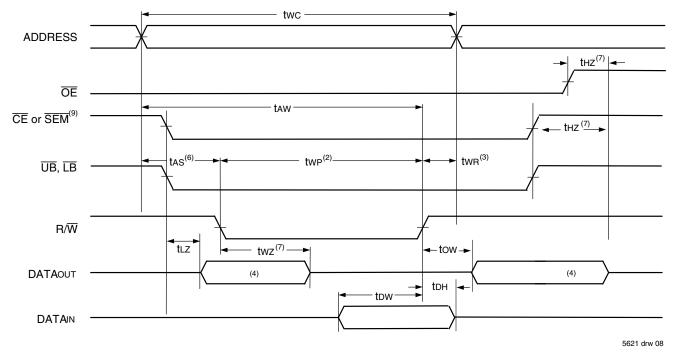
NOTES:

- 1. Timing depends on which signal is asserted last, $\overline{\text{OE}}$, $\overline{\text{CE}}$, $\overline{\text{LB}}$ or $\overline{\text{UB}}$.
- 2. Timing depends on which signal is de-asserted first CE, OE, LB or UB.
- 3. tBDD delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA or tBDD.
- 5. $\overline{\text{SEM}} = \text{VIH}.$

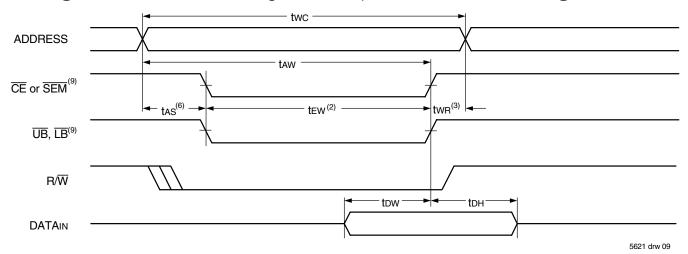
Timing of Power-Up Power-Down



Timing Waveform of Write Cycle No. 1, R/\overline{W} Controlled Timing^(1,5,8)

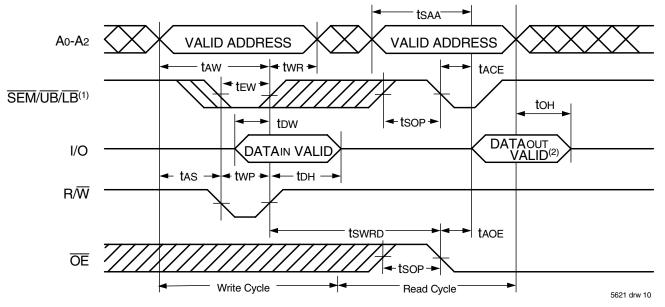


Timing Waveform of Write Cycle No. 2, CE Controlled Timing^(1,5)



- 1. R/W or \overline{CE} or \overline{UB} and \overline{LB} = VIH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a CE = VIL and a R/W = VIL for memory array writing cycle.
- 3. twR is measured from the earlier of CE or R/W (or SEM or R/W) going HIGH to the end of write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE or SEM = VIL transition occurs simultaneously with or after the R/W = VIL transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, \overline{CE} or R/\overline{W} .
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If OE = V_{IL} during R/W controlled write cycle, the write pulse width must be the larger of twp or (twz + tbw) to allow the I/O drivers to turn off and data to be placed on the bus for the required tbw. If OE = V_{IH} during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM, CE = VIL and SEM = VIH. To access semaphore, CE = VIH and SEM = VIL. tew must be met for either condition.

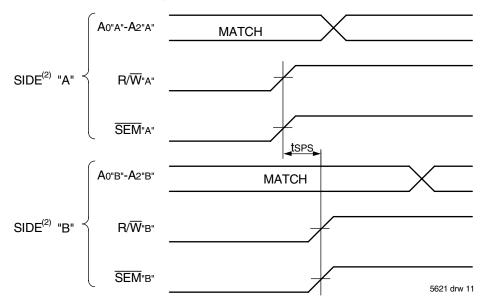
Timing Waveform of Semaphore Read after Write Timing, Either Side⁽¹⁾



NOTES:

- 1. CE = VIH or UB and LB = VIH for the duration of the above timing (both write and read cycle) (Refer to Chip Enable Truth Table). Refer also to Truth Table II for appropriate UB/LB controls.
- 2. "DATAOUT VALID" represents all I/O's (I/Oo I/O17) equal to the semaphore value.

Timing Waveform of Semaphore Write Contention^(1,3,4)



- 1. DOR = DOL = VIL, $\overline{CE}L = \overline{CE}R = VIH$. Refer also to Truth Table II for appropriate $\overline{UB}/\overline{LB}$ controls.
- 2. All timing is the same for left and right ports. Port "A" may be either left or right port. "B" is the opposite from port "A".
- 3. This parameter is measured from R/W"A" or \overline{SEM} "A" going HIGH to R/W"B" or \overline{SEM} "B" going HIGH.
- 4. If tsps is not satisfied, the semaphore will fall positively to one side or the other, but there is no guarantee which side will be granted the semaphore flag.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

		70V639S10 Com'l Only		70V639S12 Com'l & Ind		70V639S15 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
BUSY TIMING	G (M/Ś=Viн)							
tBAA	BUSY Access Time from Address Match		10		12		15	ns
tBDA	BUSY Disable Time from Address Not Matched		10		12	_	15	ns
tBAC	BUSY Access Time from Chip Enable Low		10		12		15	ns
tBDC	BUSY Disable Time from Chip Enable High		10		12		15	ns
taps	Arbitration Priority Set-up Time ⁽²⁾	5		5		5		ns
tBDD	BUSY Disable to Valid Data ⁽³⁾		10		12	—	15	ns
twн	Write Hold After BUSY ⁽⁵⁾	8		10		12		ns
BUSY TIMING	G (M/S=VIL)							
twв	BUSY Input to Write ⁽⁴⁾	0		0	—	0		ns
twн	Write Hold After BUSY ⁽⁵⁾	8		10		12		ns
PORT-TO-POR	RT DELAY TIMING							
twdd	Write Pulse to Data Delay ⁽¹⁾		22		25	—	30	ns
tDDD	Write Data Valid to Read Data Delay ⁽¹⁾		20		22	—	25	ns
	•	•	-	-	-	-	-	5621 tbl 14

NOTES:

1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY (M/S = VIH)".

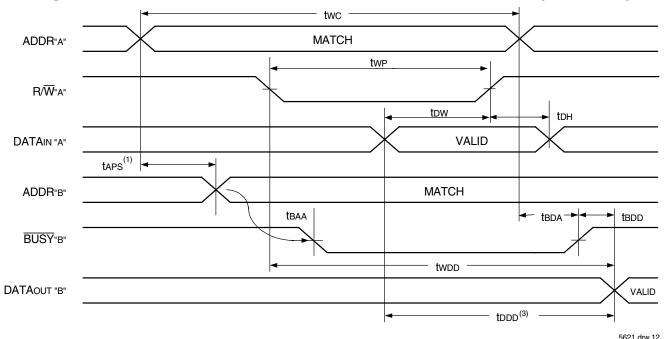
 $2. \ \ {\rm To \ ensure \ that \ the \ earlier \ of \ the \ two \ ports \ wins.}$

3. tBDD is a calculated parameter and is the greater of the Max. spec, twDD - twP (actual), or tDDD - tDw (actual).

4. To ensure that the write cycle is inhibited on port "B" during contention on port "A".

5. To ensure that a write cycle is completed on port "B" after contention on port "A".

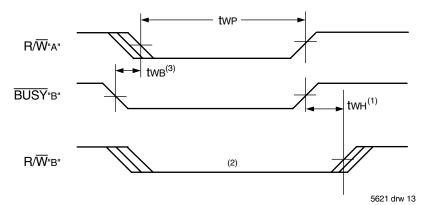
Timing Waveform of Write with Port-to-Port Read and $\overline{\text{BUSY}}$ (M/ $\overline{\text{S}}$ = VIH)^(2,4,5)



NOTES:

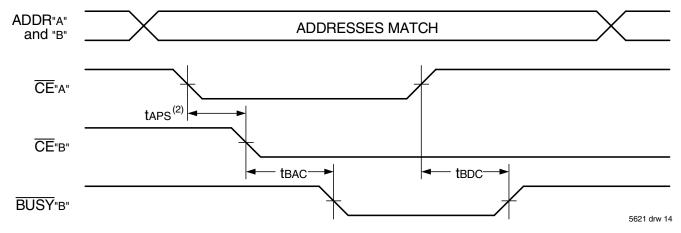
- 1. To ensure that the earlier of the two ports wins. tAPS is ignored for M/\overline{S} = VIL (SLAVE).
- 2. $\overline{CE}_{L} = \overline{CE}_{R} = V_{IL}$.
- 3. $\overline{OE} = V_{IL}$ for the reading port.
- 4. If M/S = VIL (slave), BUSY is an input. Then for this example BUSY"A" = VIH and BUSY"B" input is shown above.
- 5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

Timing Waveform of Write with $\overline{\text{BUSY}}$ (M/ $\overline{\text{S}}$ = VIL)

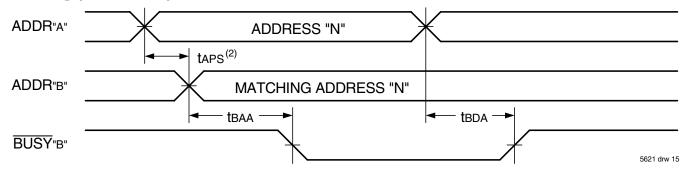


- 1. twH must be met for both BUSY input (SLAVE) and output (MASTER).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. two is only for the 'slave' version.

Waveform of $\overline{\text{BUSY}}$ Arbitration Controlled by $\overline{\text{CE}}$ Timing (M/ $\overline{\text{S}}$ = VIH)⁽¹⁾



Waveform of $\overline{\text{BUSY}}$ Arbitration Cycle Controlled by Address Match Timing (M/S = VIH)⁽¹⁾



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

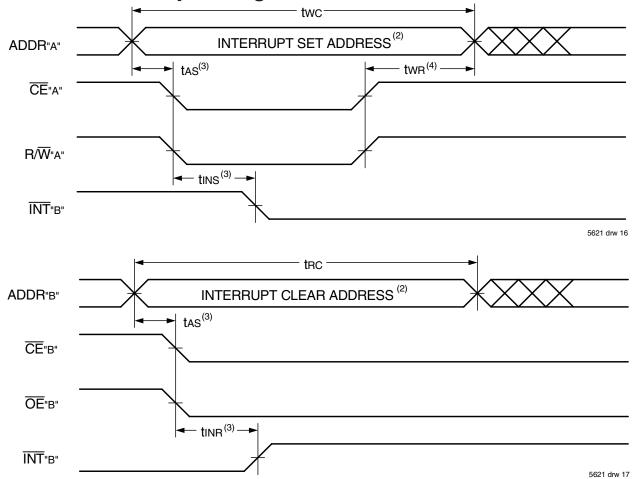
2. If tAPS is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

			39S10 'I Only	Co	39S12 om'l Ind	Co	39S15 om'l Ind	
Symbol	Parameter Min. Max. Min. Max.				Min.	Max.	Unit	
INTERRUPT T	IMING	-			-			
tas	Address Set-up Time	0		0		0		ns
twR	Write Recovery Time	0		0		0		ns
tins	Interrupt Set Time		10		12		15	ns
tinr	Interrupt Reset Time		10		12		15	ns

5621 tbl 15

Waveform of Interrupt Timing⁽¹⁾



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

2. Refer to Interrupt Truth Table.

- 3. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last.
- 4. Timing depends on which enable signal (CE or R/W) is de-asserted first.

Left Port							Right Por	t		
R/₩L	<u></u> <u> </u>	OEL	A16L-A0L	ĪNTL	R/WR	ĈĒr	ŌĒR	A16R-A0R	ĪNTR	Function
L	L	Х	1FFFF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	1FFFF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	1FFFE	Х	Set Left INTL Flag
Х	L	L	1FFFE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INTL Flag

Truth Table III — Interrupt Flag^(1,4)

NOTES:

1. Assumes $\overline{\text{BUSY}}_{L} = \overline{\text{BUSY}}_{R} = V_{IH}$.

2. If $\overline{\text{BUSY}}_{L} = V_{IL}$, then no change.

3. If $\overline{\text{BUSY}}_{R} = V_{IL}$, then no change.

4. INTL and INTR must be initialized at power-up.

5621 tbl 16

Truth Table IV — Address BUSY Arbitration

	In	puts	Out	puts	
CEL	ĊĒr	Aol-A16L Aor-A16r	BUS YL ⁽¹⁾	BUS YR ⁽¹⁾	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

5621 tbl 17

1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSY outputs on the IDT70V639 are push-pull, not open drain outputs. On slaves the BUSY input internally inhibits writes.

- "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYL outputs can not be LOW simultaneously.
- 3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

Truth Table V — Example of Semaphore Procurement Sequence^(1,2,3)

Functions	Do - D17 Left	Do - D17 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES:

1. This table denotes a sequence of events for only one of the eight semaphores on the IDT70V639.

2. There are eight semaphore flags written to via I/Oo and read from all I/O's (I/Oo-I/O17). These eight semaphores are addressed by Ao - A2.

3. TE = VIH, SEM = VIL to access the semaphores. Refer to the Semaphore Read/Write Control Truth Table.

Functional Description

The IDT70V639 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT70V639 has an automatic power down feature controlled by \overline{CE} . The \overline{CE}_0 and CE1 control the on-chip power down circuitry that permits the respective port to go into a standby mode when not selected (\overline{CE} = HIGH). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ($\overline{INT}L$) is asserted when the right port writes to memory location

3FFFE (HEX), where a write is defined as $\overline{CER} = R/\overline{WR} = VIL$ per the Truth Table. The left port clears the interrupt through access of address location 3FFFE when $\overline{CEL} = \overline{OEL} = VIL$, R/\overline{W} is a "don't care". Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location 3FFFF (HEX) and to clear the interrupt flag (\overline{INTR}), the right port must read the memory location 3FFFF. The message (18 bits) at 3FFFE or 3FFFF is user-defined since it is an addressable SRAM location. If the interrupt function is not used, address locations 3FFFE and 3FFFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table III for the interrupt operation.

5621 tbl 18

High-Speed 3.3V 128K x 18 Asynchronous Dual-Port Static RAM

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a BUSY indication, the write signal is gated internally to prevent the write from proceeding.

The use of $\overline{\text{BUSY}}$ logic is not required or desirable for all applications. In some cases it may be useful to logically OR the $\overline{\text{BUSY}}$ outputs together and use any $\overline{\text{BUSY}}$ indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of $\overline{\text{BUSY}}$ logic is not desirable, the $\overline{\text{BUSY}}$ logic can be disabled by placing the part in slave mode with the M/\overline{S} pin. Once in slave mode the $\overline{\text{BUSY}}$ pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the $\overline{\text{BUSY}}$ pins HIGH. If desired, unintended write operations can be prevented to a port by tying the $\overline{\text{BUSY}}$ pin for that port LOW.

The BUSY outputs on the IDT70V639 RAM in master mode, are push-pull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

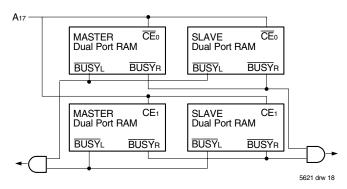


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT70V639 RAMs.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an IDT70V639 RAM array in width while using BUSY logic, one master part is used to decide which side of the RAMs array will receive a BUSY indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master use the BUSY signal as a write inhibit signal. Thus on the IDT70V639 RAM the BUSY pin is an output if the part is used as a master (M/S pin = VIH), and the BUSY pin is an input if the part used as a slave (M/S pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating BUSY on one side of the array and another master indicating BUSY on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration on a master is based on the chip enable and

address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a $\overline{\text{BUSY}}$ flag to be output from the master before the actual write pulse can be initiated with the R/\overline{W} signal. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Semaphores

The IDT70V639 is an extremely fast Dual-Port 128K x 18 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, with both ports being completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from or written to at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by \overline{CE} , the Dual-Port RAM enable, and \overline{SEM} , the semaphore enable. The \overline{CE} and \overline{SEM} pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected.

Systems which can best use the IDT70V639 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT70V639s hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT70V639 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very high-speed systems.

How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that a shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then

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Industrial and Commercial Temperature Ranges

verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active LOW. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

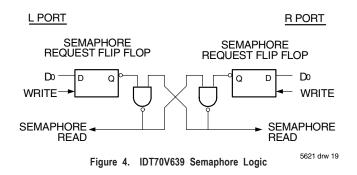
The eight semaphore flags reside within the IDT70V639 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a low input on the $\overline{\text{SEM}}$ pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address, $\overline{\text{CE}}$, R/W and $\overline{\text{LB}}/\overline{\text{UB}}$) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0 – A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin D0 is used. If a low level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Truth Table V). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore, byte select (SEM, LB/UB) and output enable (\overline{OE}) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (SEM or \overline{OE}) to go inactive or the output will never change. However, during reads LB and UB function only as an output for semaphore. They do not have any influence on the semaphore control logic.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Table V). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will



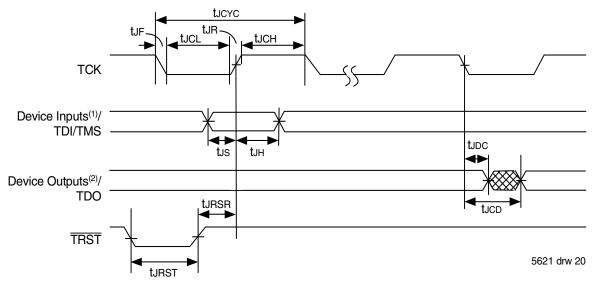
continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay LOW until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

JTAG Timing Specifications



NOTES:

- 1. Device inputs = All device inputs except TDI, TMS, and TRST.
- 2. Device outputs = All device outputs except TDO.

Symbol	Parameter	Min.	Max.	Units
tucyc	JTAG Clock Input Period	100		ns
tлсн	JTAG Clock HIGH	40		ns
tJCL	JTAG Clock Low	40		ns
IJR	JTAG Clock Rise Time		3(1)	ns
IJF	JTAG Clock Fall Time		3(1)	ns
turst	JTAG Reset	50		ns
tursr	JTAG Reset Recovery	50		ns
tJCD	JTAG Data Output		25	ns
tudc	JTAG Data Output Hold	0		ns
tus	JTAG Setup	15		ns
tлн	JTAG Hold	15		ns

JTAG AC Electrical Characteristics^(1,2,3,4)

NOTES:

- 1. Guaranteed by design.
- 2. 30pF loading on external output signals.
- 3. Refer to AC Electrical Test Conditions stated earlier in this document.
- 4. JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.

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High-Speed 3.3V 128K x 18 Asynchr	onous Dual-Port Static RAM	Industrial and Commercial Temperature Ranges
Identification Registe	er Definitions	
Instruction Field	Value	Description
Revision Number (31:28)	0x0	Reserved for version number
IDT Device ID (27:12)	0x30C	Defines IDT part number
IDT JEDEC ID (11:1)	0x33	Allows unique identification of device vendor as IDT
ID Register Indicator Bit (Bit 0)	1	Indicates the presence of an ID register

5621 tbl 20

5621 tbl 22

Scan Register Sizes

IDT70V639S

Register Name	Bit Size
Instruction (IR)	4
Bypass (BYR)	1
Identification (IDR)	32
Boundary Scan (BSR)	Note (3)

5621 tbl 21

System Interface Parameters

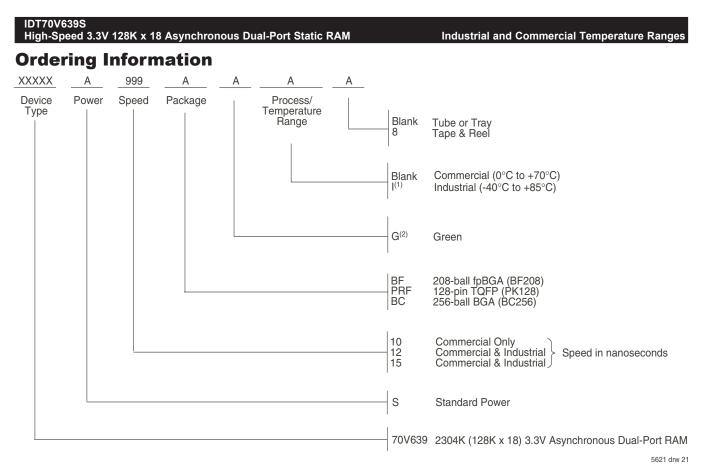
Instruction	Code	Description
EXTEST	0000	Forces contents of the boundary scan cells onto the device outputs ⁽¹⁾ . Places the boundary scan register (BSR) between TDI and TDO.
BYPASS	1111	Places the bypass register (BYR) between TDI and TDO.
IDCODE	0010	Loads the ID register (IDR) with the vendor ID code and places the register between TDI and TDO.
HIGHZ	0100	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers to a High-Z state.
CLAMP	0011	Uses BYR. Forces contents of the boundary scan cells onto the device outputs. Places the bypass register (BYR) between TDI and TDO.
SAMPLE/PRELOAD	0001	Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ⁽²⁾ and outputs ⁽¹⁾ to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.
RESERVED	All other codes	Several combinations are reserved. Do not use codes other than those identified above.

NOTES:

1. Device outputs = All device outputs except TDO.

2. Device inputs = All device inputs except TDI, TMS, and $\overline{\text{TRST}}.$

3. The Boundary Scan Descriptive Language (BSDL) file for this device is available on the IDT website (www.idt.com), or by contacting your local IDT sales representative.



NOTES:

1. Contact your local sales office for industrial temp range for other speeds, packages and powers.

2. Green parts available. For specific speeds, packages and powers contact your local sales office.

Datasheet Document History

06/01/00: 08/07/00:	Initial Public Offering Pages 6,13 & 20 Inserted additional LB and UB information
06/20/01:	Page 1 Added JTAG information for TQFP package
	Page 14 Increased BUSY TIMING parameters tBDA, tBAC, tBDC and tBDD for all speeds
	Page 21 Changed maximum value for JTAG AC Electrical Characteristics for tuch from 20ns to 25ns
10/25/04:	Removed Preliminary status
	Added date revision for pin configurations
	Page 7 Added Junction Temp to the Absolute Maximum Ratings table
	Updated Capacitance table
	Page 12 Updated Timing Waveform of Write Cycle No. 1, R/W Controlled Timing
	Page 1 & 23 Replaced old TM logo with new TM logo
05/25/05:	Page 1 Added green availability to features
	Page 23 Added green indicator to ordering information
07/25/08:	Page 8 Corrected a typo in the DC Chars table

Datasheet Document History (con't)

- 01/19/09: Page 23 Removed "IDT" from orderable part number
- 06/17/15: Page 2 Corrected text typo
 - Page 2, 3, 4 & 23 The package codes for BF-208 changed to BF208, PK-128 changed to PK128 & BC-256 changed to BC256 respectively to match the standard package codes
 - Page 2, 3 & 4 Removed the date from all of the pin configurations BF208, PK128 & BC256
 - Page 8 Corrected typo in column heading for 15ns I-temp offering
 - Page 22 Added T&R indicator and industrial temp footnote to Ordering Information



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